

High-Voltage Amplifier Transistor (150V, 50mA)

2SC5274

●Features

- 1) High breakdown voltage. ($BV_{CEO}=150V$)
- 2) Low collector output capacitance, typically 2pF at $V_{CE}=12V$.

●Packaging specifications and hFE

Type	2SC5274
Package	EMT3
hFE	N
Marking	BV*
Code	TL
Basic ordering unit (pieces)	3000

* Denotes hFE

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	150	—	—	V	$I_C=50\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	150	—	—	V	$I_C=1mA$
Emitter-base breakdown voltage	BV_{EBO}	5	—	—	V	$I_E=50\mu A$
Collector cutoff current	I_{CBO}	—	—	0.5	μA	$V_{CB}=100V, I_E=0A$
Emitter cutoff current	I_{EBO}	—	—	0.5	μA	$V_{EB}=4V, I_C=0A$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	0.5	V	$I_C/I_E=10mA/1mA$
DC current transfer ratio	hFE	56	—	120	—	$V_{CE}/I_C=10V/10mA$
Transition frequency	f_T	—	120	—	MHz	$V_{CE}=12V, I_E=-10mA, f=30MHz$
Output capacitance	C_{ob}	—	2	—	pF	$V_{CB}=12V, I_E=0A, f=1MHz$

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	150	V
Collector-emitter voltage	V_{CEO}	150	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	50	mA (DC)
		0.2	A (Pulse) *
Collector power dissipation	P_C	0.15	W
Junction temperature	TJ	150	°C
Storage temperature	Tstg	-55~+150	°C

* Single pulse Pw=100ms

(96-203-C329)